74AVC1T45

Dual-supply voltage level translator/transceiver; 3-state Rev. 3 — 21 October 2011 Product date

Product data sheet

General description 1.

The 74AVC1T45 is a single bit, dual supply transceiver with 3-state output that enables bidirectional level translation. It features two 1-bit input-output ports (A and B), a direction control input (DIR) and dual supply pins ($V_{CC(A)}$ and $V_{CC(B)}$). Both $V_{CC(A)}$ and $V_{CC(B)}$ can be supplied at any voltage between 0.8 V and 3.6 V making the device suitable for translating between any of the low voltage nodes (0.8 V, 1.2 V, 1.5 V, 1.8 V, 2.5 V and 3.3 V). Pins A and DIR are referenced to V_{CC(A)} and pin B is referenced to V_{CC(B)}. A HIGH on DIR allows transmission from A to B and a LOW on DIR allows transmission from B to Α.

The device is fully specified for partial power-down applications using I_{OFF}. The I_{OFF} circuitry disables the output, preventing any damaging backflow current through the device when it is powered down. In suspend mode when either $V_{CC(A)}$ or $V_{CC(B)}$ are at GND level, both A and B are in the high-impedance OFF-state.

Features and benefits 2.

- Wide supply voltage range:
 - ◆ V_{CC(A)}: 0.8 V to 3.6 V
 - ♦ V_{CC(B)}: 0.8 V to 3.6 V
- High noise immunity
- Complies with JEDEC standards:
 - JESD8-12 (0.8 V to 1.3 V)
 - ◆ JESD8-11 (0.9 V to 1.65 V)
 - ◆ JESD8-7 (1.2 V to 1.95 V)
 - ◆ JESD8-5 (1.8 V to 2.7 V)
 - ◆ JESD8-B (2.7 V to 3.6 V)
- ESD protection:
 - HBM JESD22-A114E Class 3B exceeds 8000 V
 - MM JESD22-A115-A exceeds 200 V
 - CDM JESD22-C101C exceeds 1000 V
- Maximum data rates:
 - ◆ 500 Mbit/s (1.8 V to 3.3 V translation)
 - ◆ 320 Mbit/s (< 1.8 V to 3.3 V translation)</p>
 - 320 Mbit/s (translate to 2.5 V or 1.8 V)
 - 280 Mbit/s (translate to 1.5 V)
 - 240 Mbit/s (translate to 1.2 V)
- Suspend mode
- Latch-up performance exceeds 100 mA per JESD 78 Class II



Dual-supply voltage level translator/transceiver; 3-state

- Inputs accept voltages up to 3.6 V
- Low noise overshoot and undershoot < 10 % of V_{CC}
- I_{OFF} circuitry provides partial Power-down mode operation
- Multiple package options
- Specified from -40 °C to +85 °C and -40 °C to +125 °C

3. Ordering information

Table 1. Ordering information

Type number	Package	Package						
	Temperature range	Name	Description	Version				
74AVC1T45GW	–40 °C to +125 °C	SC-88	plastic surface-mounted package; 6 leads	SOT363				
74AVC1T45GM	–40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 \times 1.45 \times 0.5 mm	SOT886				
74AVC1T45GN	–40 °C to +125 °C	XSON6	extremely thin small outline package; no leads; 6 terminals; body $0.9 \times 1.0 \times 0.35$ mm	SOT1115				
74AVC1T45GS	–40 °C to +125 °C	XSON6	extremely thin small outline package; no leads; 6 terminals; body $1.0 \times 1.0 \times 0.35$ mm	SOT1202				

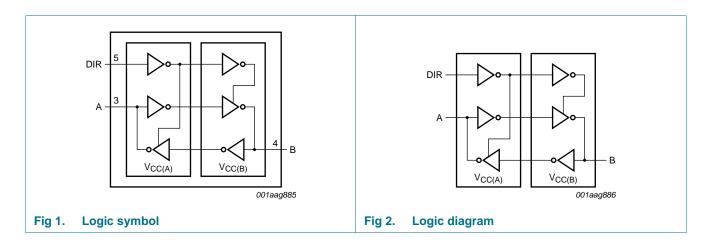
4. Marking

Table 2. Marking

Type number	Marking code ^[1]
74AVC1T45GW	B5
74AVC1T45GM	B5
74AVC1T45GN	B5
74AVC1T45GS	B5

^[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

5. Functional diagram

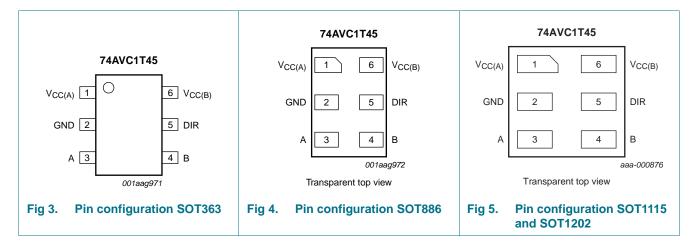


74AVC1T45

Dual-supply voltage level translator/transceiver; 3-state

6. Pinning information

6.1 Pinning



6.2 Pin description

Table 3. Pin description

Symbol	Pin	Description
$V_{CC(A)}$	1	supply voltage port A and DIR
GND	2	ground (0 V)
A	3	data input or output
В	4	data input or output
DIR	5	direction control
$V_{CC(B)}$	6	supply voltage port B

7. Functional description

Table 4. Function table [1]

Supply voltage	Input	Input/output[2]		
V _{CC(A)} , V _{CC(B)}	DIR[3]	Α	В	
0.8 V to 3.6 V	L	A = B	input	
0.8 V to 3.6 V	Н	input	B = A	
GND[4]	X	Z	Z	

- [1] H = HIGH voltage level; L = LOW voltage level; X = don't care; Z = high-impedance OFF-state.
- [2] The input circuit of the data I/O is always active.
- [3] The DIR input circuit is referenced to V_{CC(A)}.
- [4] When either $V_{CC(A)}$ or $V_{CC(B)}$ is at GND level, the device goes into suspend mode.

Dual-supply voltage level translator/transceiver; 3-state

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CC(A)}$	supply voltage A		-0.5	+4.6	V
V _{CC(B)}	supply voltage B		-0.5	+4.6	V
I _{IK}	input clamping current	V _I < 0 V	-50	-	mA
VI	input voltage		<u>[1]</u> –0.5	+4.6	V
I _{OK}	output clamping current	V _O < 0 V	-50	-	mA
Vo	output voltage	Active mode	[1][2][3] =0.5	$V_{CCO} + 0.5$	V
		Suspend or 3-state mode	<u>[1]</u> –0.5	+4.6	V
Io	output current	$V_O = 0 V \text{ to } V_{CCO}$	-	±50	mA
I _{CC}	supply current	I _{CC(A)} or I _{CC(B)}	-	100	mA
I _{GND}	ground current		-100	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	$T_{amb} = -40 ^{\circ}\text{C} \text{ to } +125 ^{\circ}\text{C}$	<u>[4]</u> _	250	mW

^[1] The minimum input voltage ratings and output voltage ratings may be exceeded if the input and output current ratings are observed.

9. Recommended operating conditions

Table 6. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CC(A)}$	supply voltage A		0.8	3.6	V
$V_{CC(B)}$	supply voltage B		0.8	3.6	V
VI	input voltage		0	3.6	V
Vo	output voltage	Active mode	<u>[1]</u> 0	V_{CCO}	V
		Suspend or 3-state mode	0	3.6	V
T _{amb}	ambient temperature		-40	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	$V_{CCI} = 0.8 \text{ V to } 3.6 \text{ V}$	[2] -	5	ns/V

^[1] V_{CCO} is the supply voltage associated with the output port.

^[2] V_{CCO} is the supply voltage associated with the output port.

^[3] V_{CCO} + 0.5 V should not exceed 4.6 V.

^[4] For SC-88 packages: above 87.5 °C the value of P_{tot} derates linearly with 4.0 mW/K. For XSON6 packages: above 118 °C the value of P_{tot} derates linearly with 7.8 mW/K.

^[2] V_{CCI} is the supply voltage associated with the input port.

Dual-supply voltage level translator/transceiver; 3-state

10. Static characteristics

Table 7. Typical static characteristics at $T_{amb} = 25 \, ^{\circ}C_{amb}^{[1][2]}$

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{OH}	HIGH-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		$I_{O} = -1.5 \text{ mA}; V_{CC(A)} = V_{CC(B)} = 0.8 \text{ V}$	-	0.69	-	V
V_{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		$I_{O} = 1.5 \text{ mA}; V_{CC(A)} = V_{CC(B)} = 0.8 \text{ V}$	-	0.07	-	V
l _l	input leakage current	DIR input; $V_1 = 0 \text{ V or } 3.6 \text{ V}$; $V_{CC(A)} = V_{CC(B)} = 0.8 \text{ V to } 3.6 \text{ V}$	-	±0.025	±0.25	μΑ
I _{OZ}	OFF-state output current	A or B port; $V_O = 0$ V or V_{CCO} ; $V_{CC(A)} = V_{CC(B)} = 0.8$ V to 3.6 V	<u>[3]</u> _	±0.5	±2.5	μΑ
l _{OFF}	power-off leakage current	A port; V_1 or $V_0 = 0$ V to 3.6 V; $V_{CC(A)} = 0$ V; $V_{CC(B)} = 0.8$ V to 3.6 V	-	±0.1	±1	μΑ
		B port; V_1 or $V_0 = 0$ V to 3.6 V; $V_{CC(B)} = 0$ V; $V_{CC(A)} = 0.8$ V to 3.6 V	-	±0.1	±1	μΑ
C _I	input capacitance	DIR input; $V_1 = 0 \text{ V or } 3.3 \text{ V}$; $V_{CC(A)} = V_{CC(B)} = 3.3 \text{ V}$	-	1.0	-	pF
C _{I/O}	input/output capacitance	A and B port; Suspend mode; $V_O = V_{CCO}$ or GND; $V_{CC(A)} = V_{CC(B)} = 3.3 \text{ V}$	-	4.0	-	pF

^[1] V_{CCO} is the supply voltage associated with the output port.

Table 8. Static characteristics [1][2]

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	–40 °C to	+85 °C	–40 °C to	+125 °C	Unit
			Min	Max	Min	Max	
V_{IH}	HIGH-level	data input					
input voltage	$V_{CCI} = 0.8 \text{ V}$	0.70V _{CCI}	-	$0.70V_{CCI}$	-	V	
		$V_{CCI} = 1.1 \text{ V to } 1.95 \text{ V}$	0.65V _{CCI}	-	0.65V _{CCI}	-	V
		$V_{CCI} = 2.3 \text{ V to } 2.7 \text{ V}$	1.6	-	1.6	-	V
		$V_{CCI} = 3.0 \text{ V to } 3.6 \text{ V}$	2	-	2	-	V
		DIR input					
		$V_{CC(A)} = 0.8 \text{ V}$	$0.70V_{CC(A)}$	-	$0.70V_{CC(A)}$	-	V
		$V_{CC(A)} = 1.1 \text{ V to } 1.95 \text{ V}$	$0.65V_{CC(A)}$	-	$0.65V_{CC(A)}$	-	V
		$V_{CC(A)} = 2.3 \text{ V to } 2.7 \text{ V}$	1.6	-	1.6	-	V
		$V_{CC(A)} = 3.0 \text{ V to } 3.6 \text{ V}$	2	-	2	-	V

^[2] V_{CCI} is the supply voltage associated with the data input port.

^[3] For I/O ports, the parameter I_{OZ} includes the input leakage current.

Dual-supply voltage level translator/transceiver; 3-state

Table 8. Static characteristics ...continued 11[2]
At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	-40 °C t	o +85 °C	–40 °C to	+125 °C	Uni
			Min	Max	Min	Max	
/ _{IL}	LOW-level	data input	'		1		
	input voltage	$V_{CCI} = 0.8 \text{ V}$	-	0.30V _{CCI}	-	0.30V _{CCI}	V
		V _{CCI} = 1.1 V to 1.95 V	-	0.35V _{CCI}	-	0.35V _{CCI}	V
		$V_{CCI} = 2.3 \text{ V to } 2.7 \text{ V}$	-	0.7	-	0.7	V
		$V_{CCI} = 3.0 \text{ V to } 3.6 \text{ V}$	-	0.9	-	0.9	V
		DIR input					
		$V_{CC(A)} = 0.8 \text{ V}$	-	0.30V _{CC(A)}	-	0.30V _{CC(A)}	V
		$V_{CC(A)} = 1.1 \text{ V to } 1.95 \text{ V}$	-	0.35V _{CC(A)}	-	0.35V _{CC(A)}	V
	DH HIGH-level output voltage	$V_{CC(A)} = 2.3 \text{ V to } 2.7 \text{ V}$	-	0.7	-	0.7	V
/он		$V_{CC(A)} = 3.0 \text{ V to } 3.6 \text{ V}$ $V_I = V_{IH} \text{ or } V_{IL}$	-	0.9	-	0.9	V
OH		$I_O = -100 \mu A;$ $V_{CC(A)} = V_{CC(B)} = 0.8 \text{ V to } 3.6 \text{ V}$	V _{CCO} - 0.1	-	V _{CCO} - 0.1	-	V
		$I_O = -3 \text{ mA};$ $V_{CC(A)} = V_{CC(B)} = 1.1 \text{ V}$	0.85	-	0.85	-	V
		$I_O = -6 \text{ mA};$ $V_{CC(A)} = V_{CC(B)} = 1.4 \text{ V}$	1.05	-	1.05	-	V
		$I_O = -8 \text{ mA};$ $V_{CC(A)} = V_{CC(B)} = 1.65 \text{ V}$	1.2	-	1.2	-	V
		$I_O = -9 \text{ mA};$ $V_{CC(A)} = V_{CC(B)} = 2.3 \text{ V}$	1.75	-	1.75	-	V
		$I_O = -12 \text{ mA};$ $V_{CC(A)} = V_{CC(B)} = 3.0 \text{ V}$	2.3	-	2.3	-	V
OL	LOW-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$ $I_{O} = 100 \mu\text{A};$	-	0.1	-	0.1	٧
		$V_{CC(A)} = V_{CC(B)} = 0.8 \text{ V to } 3.6 \text{ V}$ $I_{O} = 3 \text{ mA; } V_{CC(A)} = V_{CC(B)} = 1.1 \text{ V}$	<u>-</u>	0.25	-	0.25	V
		$I_O = 6 \text{ mA}$; $V_{CC(A)} = V_{CC(B)} = 1.1 \text{ V}$ $I_O = 6 \text{ mA}$; $V_{CC(A)} = V_{CC(B)} = 1.4 \text{ V}$	<u>-</u>	0.25	<u>-</u>	0.25	V
		$I_O = 8 \text{ mA};$ $V_{CC(A)} = V_{CC(B)} = 1.4 \text{ V}$	-	0.45	-	0.45	V
		$I_O = 9 \text{ mA}; V_{CC(A)} = V_{CC(B)} = 2.3 \text{ V}$	-	0.55	-	0.55	V
		$I_O = 12 \text{ mA};$ $V_{CC(A)} = V_{CC(B)} = 3.0 \text{ V}$	-	0.7	-	0.7	V
	input leakage current	DIR input; $V_1 = 0 \text{ V or } 3.6 \text{ V};$ $V_{CC(A)} = V_{CC(B)} = 0.8 \text{ V to } 3.6 \text{ V}$	-	±1	-	±1.5	μΔ
DΖ	OFF-state output current	A or B port; $V_O = 0 \text{ V or } V_{CCO}$; $V_{CC(A)} = V_{CC(B)} = 3.6 \text{ V}$	[3] _	±5	-	±7.5	μΑ
OFF	power-off leakage	A port; V_I or V_O = 0 V to 3.6 V; $V_{CC(A)}$ = 0 V; $V_{CC(B)}$ = 0.8 V to 3.6 V	-	±5	-	±35	μΑ
	current	B port; V_1 or $V_0 = 0$ V to 3.6 V; $V_{CC(B)} = 0$ V; $V_{CC(A)} = 0.8$ V to 3.6 V	-	±5	-	±35	μΑ

Dual-supply voltage level translator/transceiver; 3-state

Table 8. Static characteristics ...continued 11[2]
At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	–40 °C to	o +85 °C	-40 °C to	+125 °C	Unit
			Min	Max	Min	Max	
I_{CC}	supply current	A port; $V_I = 0 \text{ V or } V_{CCI}$; $I_O = 0 \text{ A}$					
		$V_{CC(A)} = 0.8 \text{ V to } 3.6 \text{ V};$ $V_{CC(B)} = 0.8 \text{ V to } 3.6 \text{ V}$	-	8	-	12	μΑ
	$V_{CC(A)} = 3.6 \text{ V}; V_{CC(B)} = 0 \text{ V}$	-	8	-	12	μΑ	
		$V_{CC(A)} = 0 \text{ V}; V_{CC(B)} = 3.6 \text{ V}$	-2	-	-8	-	μΑ
		B port; $V_I = 0 \text{ V or } V_{CCI}$; $I_O = 0 \text{ A}$					
		$V_{CC(A)} = 0.8 \text{ V to } 3.6 \text{ V};$ $V_{CC(B)} = 0.8 \text{ V to } 3.6 \text{ V}$	-	8	-	12	μΑ
		$V_{CC(A)} = 3.6 \text{ V}; V_{CC(B)} = 0 \text{ V}$	-2	-	-8	-	μΑ
		$V_{CC(A)} = 0 \text{ V}; V_{CC(B)} = 3.6 \text{ V}$	-	8	-	12	μΑ
		A plus B port ($I_{CC(A)} + I_{CC(B)}$); $I_O = 0$ A; $V_I = 0$ V or V_{CCI} ; $V_{CC(A)} = 0.8$ V to 3.6 V; $V_{CC(B)} = 0.8$ V to 3.6 V	-	16	-	24	μА

^[1] V_{CCO} is the supply voltage associated with the output port.

^[2] V_{CCI} is the supply voltage associated with the data input port.

^[3] For I/O ports, the parameter I_{OZ} includes the input leakage current.

Dual-supply voltage level translator/transceiver; 3-state

11. Dynamic characteristics

Table 9. Typical dynamic characteristics at $V_{CC(A)} = 0.8 \text{ V}$ and $T_{amb} = 25 ^{\circ}\text{C}$ [1]

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 8; for wave forms see Figure 6 and Figure 7

Symbol	Parameter	Conditions	Conditions V _{CC(B)}						Unit
			0.8 V	1.2 V	1.5 V	1.8 V	2.5 V	3.3 V	
t _{pd}	propagation delay	A to B	15.5	8.1	7.6	7.7	8.4	9.2	ns
		B to A	15.5	12.7	12.3	12.2	12.0	11.8	ns
t _{dis}	disable time	DIR to A	12.2	12.2	12.2	12.2	12.2	12.2	ns
		DIR to B	11.7	7.9	7.6	8.2	8.7	10.2	ns
t _{en}	enable time	DIR to A	27.2	20.6	19.9	20.4	20.7	22.0	ns
		DIR to B	27.7	20.3	19.8	19.9	20.6	21.4	ns

^[1] t_{pd} is the same as t_{PLH} and t_{PHL}; t_{dis} is the same as t_{PLZ} and t_{PHZ}; t_{en} is the same as t_{PZL} and t_{PZH}. t_{en} is a calculated value using the formula shown in Section 13.4 "Enable times"

Table 10. Typical dynamic characteristics at $V_{CC(B)} = 0.8 \text{ V}$ and $T_{amb} = 25 ^{\circ}\text{C}$ [1]

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 8; for wave forms see Figure 6 and Figure 7

Symbol	Parameter	Conditions			Vc	C(A)			Unit
			0.8 V	1.2 V	1.5 V	1.8 V	2.5 V	3.3 V	
t _{pd} propagation delay	propagation delay	A to B	15.5	12.7	12.3	12.2	12.0	11.8	ns
	B to A	15.5	8.1	7.6	7.7	8.4	9.2	ns	
t _{dis} disable time	disable time	DIR to A	12.2	4.9	3.8	3.7	2.8	3.4	ns
		DIR to B	11.7	9.2	9.0	8.8	8.7	8.6	ns
t _{en} enable ti	enable time	DIR to A	27.2	17.3	16.6	16.5	17.1	17.8	ns
		DIR to B	27.7	17.6	16.1	15.9	14.8	15.2	ns

^[1] t_{pd} is the same as t_{PLH} and t_{PHL}; t_{dis} is the same as t_{PLZ} and t_{PHZ}; t_{en} is the same as t_{PZL} and t_{PZH}.
t_{en} is a calculated value using the formula shown in Section 13.4 "Enable times"

Table 11. Typical power dissipation capacitance at $V_{CC(A)} = V_{CC(B)}$ and $T_{amb} = 25 \, ^{\circ}C$ [1][2]

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	V _{CC(A)} and V _{CC(B)}						
			0.8 V	1.2 V	1.5 V	1.8 V	2.5 V	3.3 V	
C_{PD}	power dissipation capacitance	A port: (direction A to B); B port: (direction B to A)	1	2	2	2	2	2	pF
		A port: (direction B to A); B port: (direction A to B)	9	11	11	12	14	17	pF

^[1] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o) \text{ where:}$

f_i = input frequency in MHz;

fo = output frequency in MHz;

C_L = load capacitance in pF;

V_{CC} = supply voltage in V;

N = number of inputs switching;

 $\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of the outputs.

[2] f_i = 10 MHz; V_I = GND to V_{CC} ; t_r = t_f = 1 ns; C_L = 0 pF; R_L = ∞ Ω .

74AVC1T45

Dual-supply voltage level translator/transceiver; 3-state

Table 12. Dynamic characteristics for temperature range –40 °C to +85 °C [1] Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 8; for wave forms see Figure 6 and Figure 7.

Symbol	Parameter	Conditions	V _{CC(B)}								Unit		
			1.2 V	± 0.1 V	1.5 V	± 0.1 V	1.8 V ±	0.15 V	2.5 V	± 0.2 V	3.3 V	± 0.3 V	
			Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
V _{CC(A)} =	1.1 V to 1.3 V	'	'						,				
t _{pd}	propagation	A to B	1.0	9.0	0.7	6.8	0.6	6.1	0.5	5.7	0.5	6.1	ns
	delay	B to A	1.0	9.0	0.8	8.0	0.7	7.7	0.6	7.2	0.5	7.1	ns
t _{dis}	disable time	DIR to A	2.2	8.8	2.2	8.8	2.2	8.8	2.2	8.8	2.2	8.8	ns
	DIR to B	2.2	8.4	1.8	6.7	2.0	6.9	1.7	6.2	2.4	7.2	ns	
t _{en}	enable time	DIR to A	-	17.4	-	14.7	-	14.6	-	13.4	-	14.3	ns
		DIR to B	-	17.8	-	15.6	-	14.9	-	14.5	-	14.9	ns
V _{CC(A)} =	1.4 V to 1.6 V												
t _{pd}	propagation	A to B	1.0	8.0	0.7	5.4	0.6	4.6	0.5	3.7	0.5	3.5	ns
	delay	B to A	1.0	6.8	8.0	5.4	0.7	5.1	0.6	4.7	0.5	4.5	ns
t _{dis}	disable time	DIR to A	1.6	6.3	1.6	6.3	1.6	6.3	1.6	6.3	1.6	6.3	ns
		DIR to B	2.0	7.6	1.8	5.9	1.6	6.0	1.2	4.8	1.7	5.5	ns
t _{en}	enable time	DIR to A	-	14.4	-	11.3	-	11.1	-	9.5	-	10.0	ns
		DIR to B	-	14.3	-	11.7	-	10.9	-	10.0	-	9.8	ns
$V_{CC(A)} =$	1.65 V to 1.95	V											
	propagation	A to B	1.0	7.7	0.6	5.1	0.5	4.3	0.5	3.4	0.5	3.1	ns
	delay	B to A	1.0	6.1	0.7	4.6	0.5	4.4	0.5	3.9	0.5	3.7	ns
t_{dis}	disable time	DIR to A	1.6	5.5	1.6	5.5	1.6	5.5	1.6	5.5	1.6	5.5	ns
		DIR to B	1.8	7.7	1.8	5.7	1.4	5.8	1.0	4.5	1.5	5.2	ns
t _{en}	enable time	DIR to A	-	13.8	-	10.3	-	10.2	-	8.4	-	8.9	ns
		DIR to B	-	13.2	-	10.6	-	9.8	-	8.9	-	8.6	ns
$V_{CC(A)} =$	2.3 V to 2.7 V												
t_{pd}	propagation	A to B	1.0	7.2	0.5	4.7	0.5	3.9	0.5	3.0	0.5	2.6	ns
	delay	B to A	1.0	5.7	0.6	3.8	0.5	3.4	0.5	3.0	0.5	2.8	ns
t _{dis}	disable time	DIR to A	1.5	4.2	1.5	4.2	1.5	4.2	1.5	4.2	1.5	4.2	ns
		DIR to B	1.7	7.3	2.0	5.2	1.5	5.1	0.6	4.2	1.1	4.8	ns
t _{en}	enable time	DIR to A	-	13.0	-	9.0	-	8.5	-	7.2	-	7.6	ns
		DIR to B	-	11.4	-	8.9	-	8.1	-	7.2	-	6.8	ns
$V_{CC(A)} =$	3.0 V to 3.6 V												
t_{pd}	propagation	A to B	1.0	7.1	0.5	4.5	0.5	3.7	0.5	2.8	0.5	2.4	ns
	delay	B to A	1.0	6.1	0.6	3.6	0.5	3.1	0.5	2.6	0.5	2.4	ns
t _{dis}	disable time	DIR to A	1.5	4.7	1.5	4.7	1.5	4.7	1.5	4.7	1.5	4.7	ns
		DIR to B	1.7	7.2	0.7	5.5	0.6	5.5	0.7	4.1	1.7	4.7	ns
t _{en}	enable time	DIR to A	-	13.3	-	9.1	-	8.6	-	6.7	-	7.1	ns
		DIR to B	-	11.8	-	9.2	-	8.4	-	7.5	-	7.1	ns

^[1] t_{pd} is the same as t_{PLH} and t_{PHL} ; t_{dis} is the same as t_{PLZ} and t_{PHZ} ; t_{en} is the same as t_{PZL} and t_{PZH} . t_{en} is a calculated value using the formula shown in Section 13.4 "Enable times"

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Table 13. Dynamic characteristics for temperature range –40 °C to +125 °C [1]

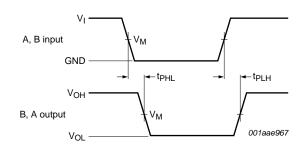
Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 8; for wave forms see Figure 6 and Figure 7

Symbol	Parameter	Conditions	V _{CC(B)}	± 0.1 V	1 5 V	± 0.1 V	1 9 V [_]	0.15 V	2 5 V	± 0.2 V	2 2 V	.2 V 3.3 V ± 0.3 V					
			Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	_				
Vacus -	1.1 V to 1.3 V			Max	141111	Wax	141111	Max		Mux		Max					
	propagation	A to B	1.0	9.9	0.7	7.5	0.6	6.8	0.5	6.3	0.5	6.8	ns				
t _{pd}	delay	B to A	1.0	9.9	0.8	8.8	0.7	8.5		8.0	0.5	7.9					
4	<u> </u>	DIR to A							0.6			9.7	ns				
t _{dis} disable time	DIR to B	2.2	9.7	2.2	9.7	2.2	9.7	2.2	9.7	2.2		ns					
1	enable time		2.2	9.2	1.8	7.4	2.0	7.6 16.1	1.7	6.9	2.4	8.0 15.9	ns				
t _{en}	enable time	DIR to A	-	19.1	-	16.2	-		-	14.9	-		ns				
V	4.4.1/1-4.6.1/	DIR to B	-	19.6	-	17.2	-	16.5	-	16.0	-	16.5	ns				
	1.4 V to 1.6 V	A D	4.0	0.0	0.7	0.0	0.0	F 4	0.5	4.4	0.5	0.0					
t _{pd}	propagation delay	A to B	1.0	8.8	0.7	6.0	0.6	5.1	0.5	4.1	0.5	3.9	ns				
		B to A	1.0	7.5	0.8	6.0	0.7	5.7	0.6	5.2	0.5	5.0	ns				
t _{dis}	disable time	DIR to A	1.6	7.0	1.6	7.0	1.6	7.0	1.6	7.0	1.6	7.0	ns				
	11. 4	DIR to B	2.0	8.3	1.8	6.5	1.6	6.6	1.2	5.3	1.7	6.1	ns				
t _{en}	enable time	DIR to A	-	15.8	-	12.5	-	12.3	-	10.5	-	11.1	ns				
		DIR to B	-	15.8	-	13.0	-	12.1	-	11.1	-	10.9	ns				
. , ,	1.65 V to 1.95																
	propagation delay	A to B	1.0	8.5	0.6	5.7	0.5	4.8	0.5	3.8	0.5	3.5	ns				
	<u> </u>	B to A	1.0	6.8	0.7	5.1	0.5	4.9	0.5	4.3	0.5	4.1	ns				
t _{dis}	disable time	DIR to A	1.6	6.1	1.6	6.1	1.6	6.1	1.6	6.1	1.6	6.1	ns				
		DIR to B	1.8	8.5	1.8	6.3	1.4	6.4	1.0	5.0	1.5	5.8	ns				
t _{en}	enable time	DIR to A	-	15.3	-	11.4	-	11.3	-	9.3	-	9.9	ns				
		DIR to B	-	14.6	-	11.8	•	10.9	-	9.9	-	9.6	ns				
$V_{CC(A)} =$	2.3 V to 2.7 V																
t_{pd}	propagation	A to B	1.0	8.0	0.5	5.2	0.5	4.3	0.5	3.3	0.5	2.9	ns				
	delay	B to A	1.0	6.3	0.6	4.2	0.5	3.8	0.5	3.3	0.5	3.1	ns				
t _{dis}	disable time	DIR to A	1.5	4.7	1.5	4.7	1.5	4.7	1.5	4.7	1.5	4.7	ns				
		DIR to B	1.7	8.0	2.0	5.8	1.5	5.7	0.6	4.7	1.1	5.3	ns				
t _{en}	enable time	DIR to A	-	14.3	-	10.0	-	9.5	-	8.0	-	8.4	ns				
		DIR to B	-	12.7	-	9.9	-	9.0	-	8.0	-	7.6	ns				
V _{CC(A)} =	3.0 V to 3.6 V																
t _{pd}	propagation	A to B	1.0	7.9	0.5	5.0	0.5	4.1	0.5	3.1	0.5	2.7	ns				
	delay	B to A	1.0	6.8	0.6	4.0	0.5	3.5	0.5	2.9	0.5	2.7	ns				
t _{dis}	disable time	DIR to A	1.5	5.2	1.5	5.2	1.5	5.2	1.5	5.2	1.5	5.2	ns				
		DIR to B	1.7	7.9	0.7	6.1	0.6	6.1	0.7	4.6	1.7	5.2	ns				
t _{en}	enable time	DIR to A	-	14.7	-	10.1	-	9.6	-	7.5	-	7.9	ns				
		DIR to B	-	13.1	-	10.2	-	9.3	-	8.3	-	7.9	ns				

^[1] t_{pd} is the same as t_{PLH} and t_{PHL} ; t_{dis} is the same as t_{PLZ} and t_{PHZ} ; t_{en} is the same as t_{PZL} and t_{PZH} . t_{en} is a calculated value using the formula shown in <u>Section 13.4 "Enable times"</u>

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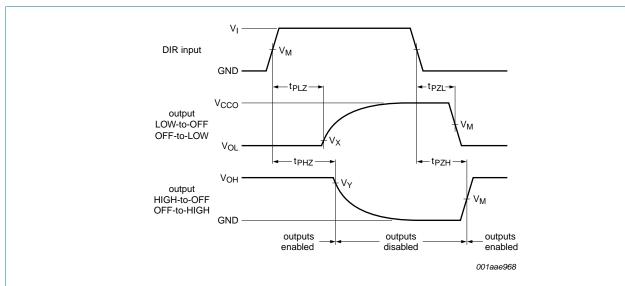
12. Waveforms



Measurement points are given in Table 14.

 V_{OL} and V_{OH} are typical output voltage drops that occur with the output load.

Fig 6. The data input (A, B) to output (B, A) propagation delay times



Measurement points are given in Table 14.

V_{OL} and V_{OH} are typical output voltage drops that occur with the output load.

Fig 7. Enable and disable times

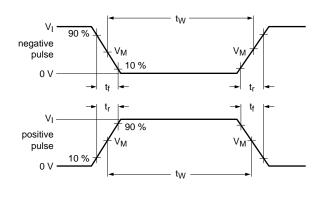
Table 14. Measurement points

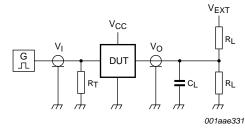
Supply voltage	Input[1]	Output ^[2]			
V _{CC(A)} , V _{CC(B)}	V _M	V _M	V _X	V _Y	
1.1 V to 1.6 V	0.5V _{CCI}	0.5V _{CCO}	V _{OL} + 0.1 V	$V_{OH} - 0.1 V$	
1.65 V to 2.7 V	0.5V _{CCI}	0.5V _{CCO}	V _{OL} + 0.15 V	V _{OH} – 0.15 V	
3.0 V to 3.6 V	0.5V _{CCI}	0.5V _{CCO}	V _{OL} + 0.3 V	V _{OH} – 0.3 V	

^[1] V_{CCI} is the supply voltage associated with the data input port.

^[2] V_{CCO} is the supply voltage associated with the output port.

Dual-supply voltage level translator/transceiver; 3-state





Test data is given in Table 15.

 R_L = Load resistance.

 C_L = Load capacitance including jig and probe capacitance.

 R_T = Termination resistance.

 V_{EXT} = External voltage for measuring switching times.

Fig 8. Test circuit for measuring switching times

Table 15. Test data

Supply voltage	Input	Input L		Load		V _{EXT}		
V _{CC(A)} , V _{CC(B)}	V _I [1]	∆t/∆V[2]	CL	R _L	t _{PLH} , t _{PHL}	t _{PZH} , t _{PHZ}	t _{PZL} , t _{PLZ} [3]	
1.1 V to 1.6 V	V_{CCI}	≤ 1.0 ns/V	15 pF	2 kΩ	open	GND	2V _{CCO}	
1.65 V to 2.7 V	V_{CCI}	≤ 1.0 ns/V	15 pF	2 kΩ	open	GND	2V _{CCO}	
3.0 V to 3.6 V	V_{CCI}	≤ 1.0 ns/V	15 pF	2 kΩ	open	GND	2V _{CCO}	

[1] V_{CCI} is the supply voltage associated with the data input port.

[2] dV/dt ≥ 1.0 V/ns

[3] V_{CCO} is the supply voltage associated with the output port.

Dual-supply voltage level translator/transceiver; 3-state

13. Application information

13.1 Unidirectional logic level-shifting application

The circuit given in Figure 9 is an example of the 74AVC1T45 being used in an unidirectional logic level-shifting application.

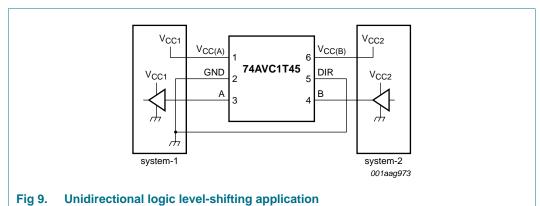


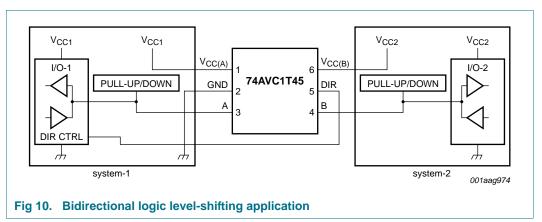
Table 16. Description unidirectional logic level-shifting application

Pin	Name	Function	Description
1	$V_{CC(A)}$	V_{CC1}	supply voltage of system-1 (0.8 V to 3.6 V)
2	GND	GND	device GND
3	Α	OUT	output level depends on V _{CC1} voltage
4	DIR	DIR	the GND (LOW level) determines B port to A port direction
5	В	IN	input threshold value depends on V _{CC2} voltage
6	$V_{CC(B)}$	V_{CC2}	supply voltage of system-2 (0.8 V to 3.6 V)

Dual-supply voltage level translator/transceiver; 3-state

13.2 Bidirectional logic level-shifting application

<u>Figure 10</u> shows the 74AVC1T45 being used in a bidirectional logic level-shifting application. Since the device does not have an output enable pin, the system designer should take precautions to avoid bus contention between system-1 and system-2 when changing directions.



<u>Table 17</u> gives a sequence that will illustrate data transmission from system-1 to system-2 and then from system-2 to system-1.

Table 17. Description bidirectional logic level-shifting application[1]

State	DIR CTRL	I/O-1	I/O-2	Description
1	Н	output	input	system-1 data to system-2
2	Н	Z	Z	system-2 is getting ready to send data to system-1. I/O-1 and I/O-2 are disabled. The bus-line state depends on bus hold.
3	L	Z	Z	DIR bit is set LOW. I/O-1 and I/O-2 still are disabled. The bus-line state depends on bus hold.
4	L	input	output	system-2 data to system-1

^[1] H = HIGH voltage level;

L = LOW voltage level;

Z = high-impedance OFF-state.

Dual-supply voltage level translator/transceiver; 3-state

13.3 Power-up considerations

The device is designed such that no special power-up sequence is required other than GND being applied first.

Table 18. Typical total supply current $(I_{CC(A)} + I_{CC(B)})$

				. ,	. ,						
V _{CC(A)}	V _{CC(B)}	V _{CC(B)}									
	0 V	0.8 V	1.2 V	1.5 V	1.8 V	2.5 V	3.3 V				
0 V	0	0.1	0.1	0.1	0.1	0.1	0.1	μΑ			
0.8 V	0.1	0.1	0.1	0.1	0.1	0.7	2.3	μΑ			
1.2 V	0.1	0.1	0.1	0.1	0.1	0.3	1.4	μΑ			
1.5 V	0.1	0.1	0.1	0.1	0.1	0.1	0.9	μΑ			
1.8 V	0.1	0.1	0.1	0.1	0.1	0.1	0.5	μΑ			
2.5 V	0.1	0.7	0.3	0.1	0.1	0.1	0.1	μΑ			
3.3 V	0.1	2.3	1.4	0.9	0.5	0.1	0.1	μΑ			

13.4 Enable times

Calculate the enable times for the 74AVC1T45 using the following formulas:

- t_{en} (DIR to A) = t_{dis} (DIR to B) + t_{pd} (B to A)
- t_{en} (DIR to B) = t_{dis} (DIR to A) + t_{pd} (A to B)

In a bidirectional application, these enable times provide the maximum delay from the time the DIR bit is switched until an output is expected. For example, if the 74AVC1T45 initially is transmitting from A to B, then the DIR bit is switched, the B port of the device must be disabled before presenting it with an input. After the B port has been disabled, an input signal applied to it appears on the corresponding A port after the specified propagation delay.

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14. Package outline

Plastic surface-mounted package; 6 leads

SOT363

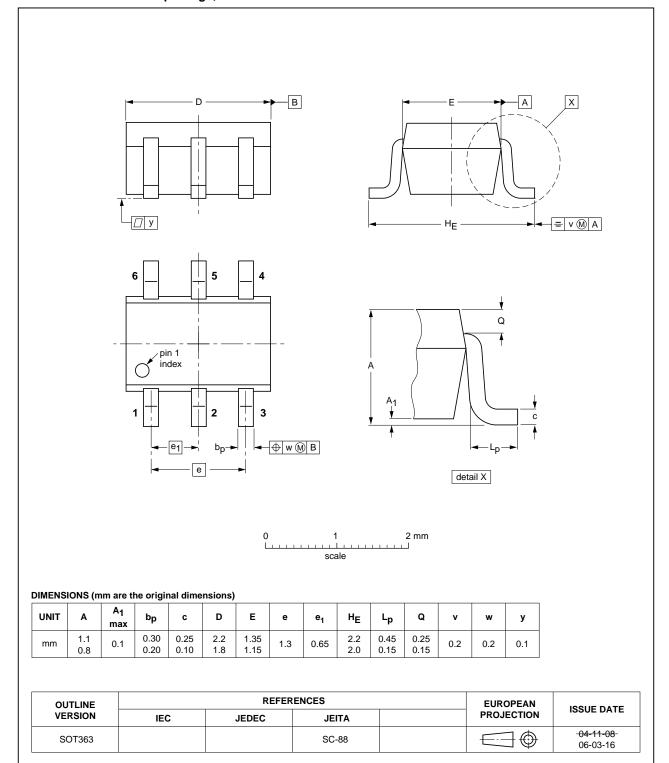


Fig 11. Package outline SOT363 (SC-88)

74AVC1T45

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Dual-supply voltage level translator/transceiver; 3-state

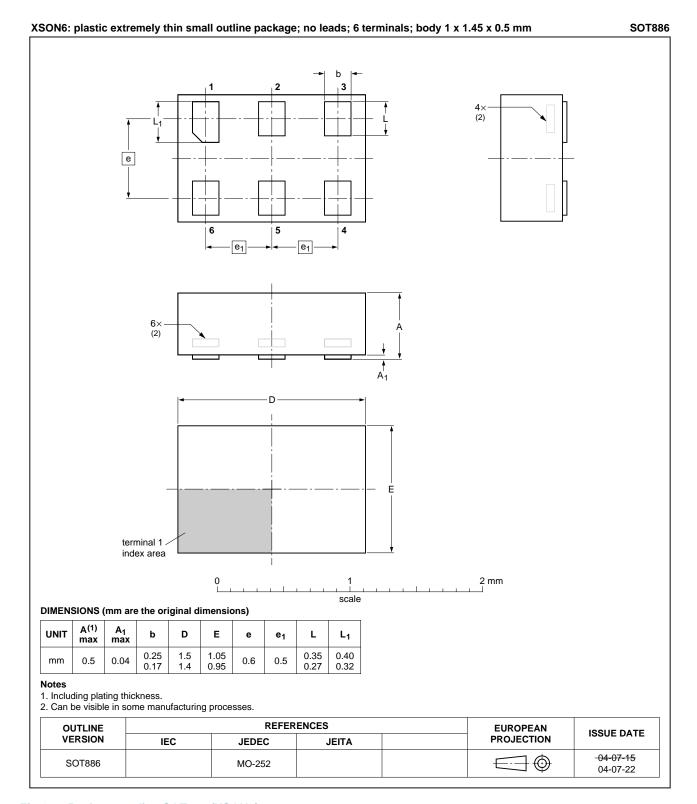


Fig 12. Package outline SOT886 (XSON6)

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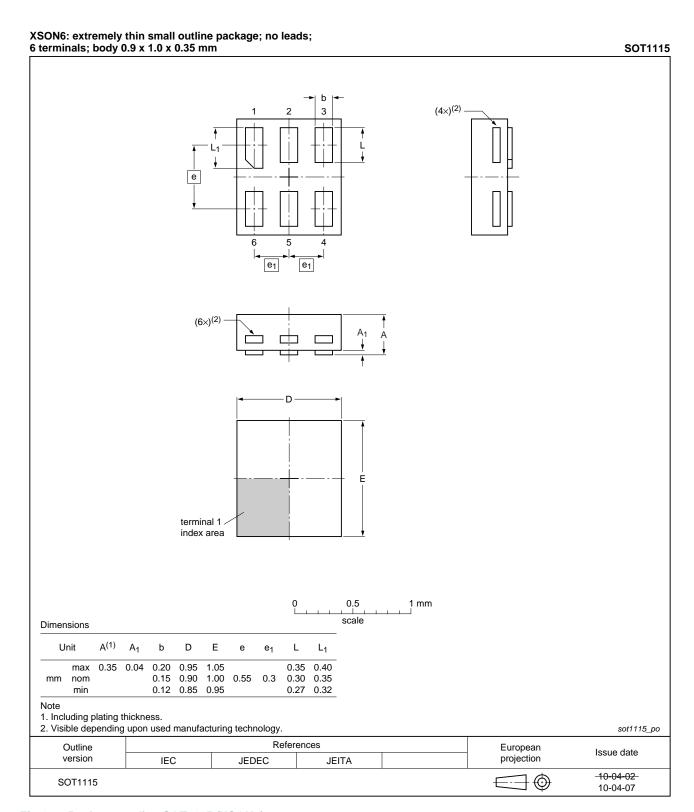


Fig 13. Package outline SOT1115 (XSON6)

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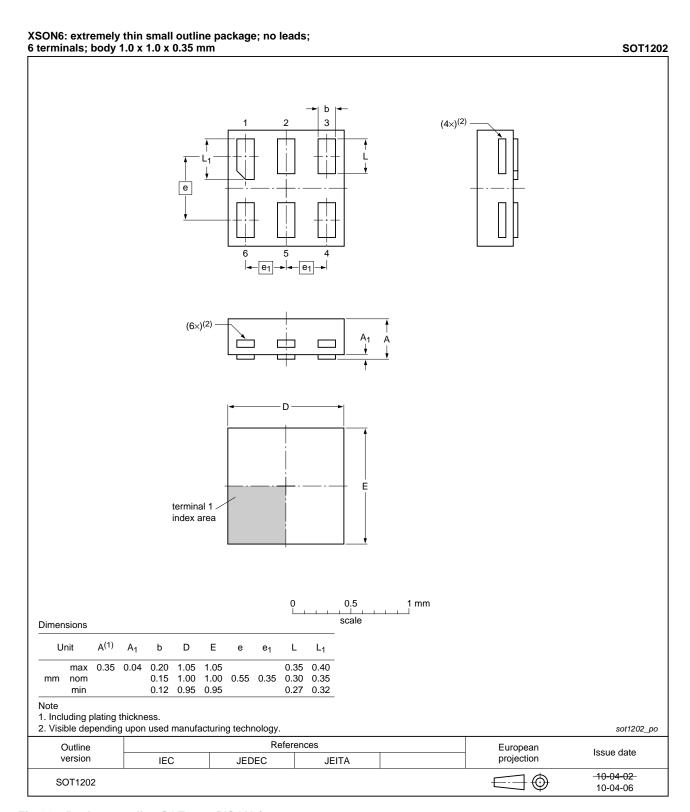


Fig 14. Package outline SOT1202 (XSON6)

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15. Abbreviations

Table 19. Abbreviations

Acronym	Description
CDM	Charged Device Model
CMOS	Complementary Metal Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
НВМ	Human Body Model
MM	Machine Model

16. Revision history

Table 20. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74AVC1T45 v.3	20111021	Product data sheet	-	74AVC1T45 v.2
Modifications:	• •	number 74AVC1T45GN (S number 74AVC1T45GS (S	. •	•
74AVC1T45 v.2	20090505	Product data sheet	-	74AVC1T45 v.1
74AVC1T45 v.1	20080118	Product data sheet	-	-

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17. Legal information

17.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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19. Contents

1	General description
2	Features and benefits
3	Ordering information 2
4	Marking 2
5	Functional diagram 2
6	Pinning information
6.1	Pinning
6.2	Pin description
7	Functional description 3
8	Limiting values 4
9	Recommended operating conditions 4
10	Static characteristics 5
11	Dynamic characteristics 8
12	Waveforms
13	Application information
13.1	Unidirectional logic level-shifting application . 13
13.2	Bidirectional logic level-shifting application 14
13.3	Power-up considerations
13.4	Enable times
14	Package outline
15	Abbreviations
16	Revision history
17	Legal information
17.1	Data sheet status 21
17.2	Definitions
17.3	Disclaimers
17.4	Trademarks22
18	Contact information 22
40	Cantonto

Please be aware that important notices concerning this document and the product(s) described herein, have been included in section 'Legal information'.